Schottky Barrier Diode

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

- Extremely Fast Switching Speed
- Extremely Low Forward Voltage -0.35 V (Typ) @ I_F = 10 mAdc
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	30	V
Forward Power Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _F	200 1.6	mW mW/°C
Forward Current (DC)	١ _F	200 Max	mA
Non–Repetitive Peak Forward Current, t _p < 10 msec	I _{FSM}	600	mA
Repetitive Peak Forward Current Pulse Wave = 1 sec, Duty Cycle = 66%	I _{FRM}	300	mA
Junction Temperature	TJ	-55 to 125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

MAXIMUM RATINGS (T_J = 125°C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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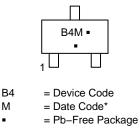
www.onsemi.com

30 VOLT SCHOTTKY BARRIER DETECTOR AND SWITCHING DIODE



SOT-323 CASE 419 STYLE 2

MARKING DIAGRAM



(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BAT54WT1G	SOT-323 (Pb-Free)	3,000 / Tape & Reel
NSVBAT54WT1G	SOT-323 (Pb-Free)	3,000 / Tape & Reel

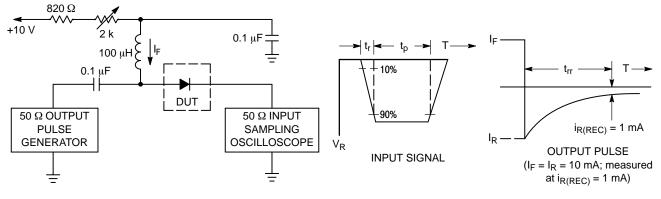
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

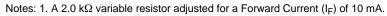
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BAT54W

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage $(I_R = 10 \ \mu A)$	V _{(BR)R}	30	-	-	V
Total Capacitance ($V_R = 1.0 V, f = 1.0 MHz$)	CT	_	7.6	10	pF
Reverse Leakage $(V_R = 25 V)$	I _R	-	0.5	2.0	μAdc
Forward Voltage $(I_F = 0.1 \text{ mA})$ $(I_F = 1.0 \text{ mA})$ $(I_F = 10 \text{ mA})$ $(I_F = 30 \text{ mA})$ $(I_F = 100 \text{ mA})$	VF	- - - - -	0.22 0.29 0.35 0.41 0.52	0.24 0.32 0.40 0.50 0.80	V
Reverse Recovery Time $(I_F = I_R = 10 \text{ mAdc}, I_{R(REC)} = 1.0 \text{ mAdc}, Figure 1)$	t _{rr}	_	-	5.0	ns







2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.

3. t_p » t_{rr}

Figure 1. Recovery Time Equivalent Test Circuit

BAT54W

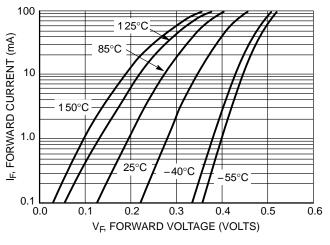


Figure 2. Forward Voltage

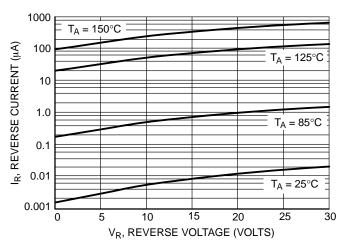


Figure 3. Leakage Current

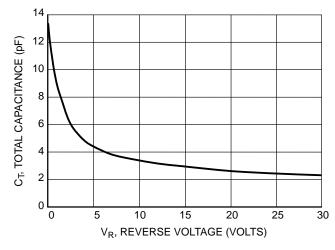
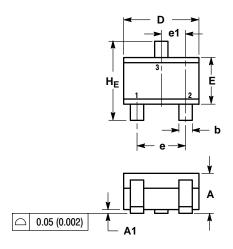


Figure 4. Total Capacitance

BAT54W

PACKAGE DIMENSIONS

SOT-323 (SC-70) CASE 419-04 ISSUE N

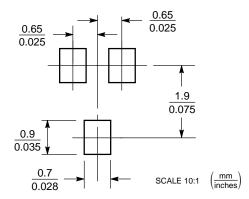


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCUSE		
				INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
Е	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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